



80V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	6.9mΩ @ V _{GS} = 10V	48A
80V	10.4mΩ @ V _{GS} = 4.5V	38A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

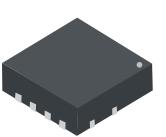
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

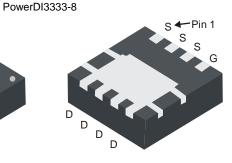
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{gd} × R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

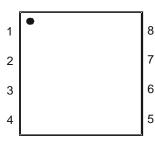
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (©3)
- Weight: 0.072 grams (Approximate)



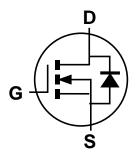




Bottom View



Top View



Equivalent Circuit

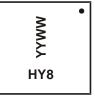
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT8008LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT8008LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



HY8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	80	V	
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 7) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		ΙD	48 38	Α
Continuous Drain Current (Note 6) $V_{GS} = 10V$ $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		I _D	16 13	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	45	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	192	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%	I _{SM}	192	Α	
Avalanche Current, L = 1mH (Note 8)	I _{AS}	18	Α	
Avalanche Energy, L = 1mH (Note 8)	Eas	162	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ hetaJA}$	126	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P_{D}	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ hetaJA}$	49	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P_{D}	23.5	W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	5.3	°C/W	
Operating and Storage Temperature Range		$T_{J_{i}}T_{STG}$	-55 to +150	°C

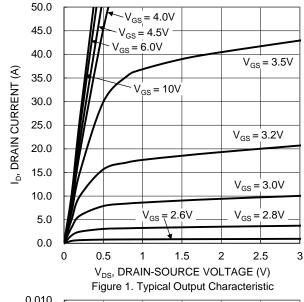
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

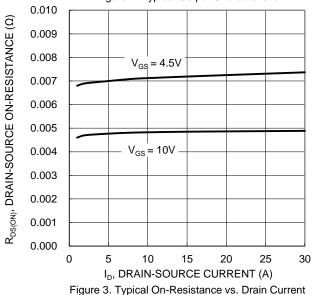
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage		80	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.2	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance			5.3	6.9	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	7.9	10.4		$V_{GS} = 4.5V, I_D = 10A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	2254	_		V _{DS} = 40V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		745	_	pF		
Reverse Transfer Capacitance	Crss	_	31	_			
Gate Resistance	Rg	_	1.98	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	18.3	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	37.7	_	~^	10)/ 1 110	
Gate-Source Charge	Q _{gs}	_	5.3	_	nC	$V_{DS} = 40V, I_{D} = 14A$	
Gate-Drain Charge	Q _{gd}	_	7.8	_			
Turn-On Delay Time	t _{D(ON)}	_	6.9	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 14A, R_{G} = 6\Omega$	
Turn-On Rise Time	t _R	_	12	_			
Turn-Off Delay Time	t _{D(OFF)}	_	37	_	ns		
Turn-Off Fall Time	t _F	_	21	_			
Body Diode Reverse Recovery Time	t _{RR}	_	42	_	ns I dan iliti donati.		
Body Diode Reverse Recovery Charge	Q_{RR}	_	53	_	nC	$I_S = 14A$, di/dt = 100A/ μ s	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.









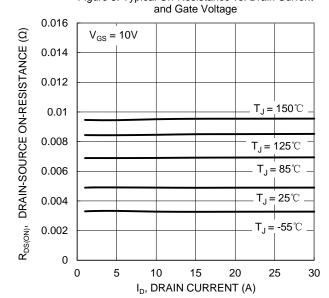
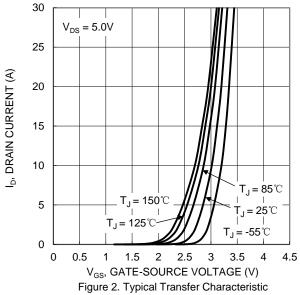


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



O.1

O.1

O.08

O.08

O.09

O.00

O.

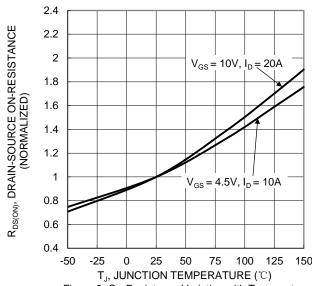


Figure 6. On-Resistance Variation with Temperature





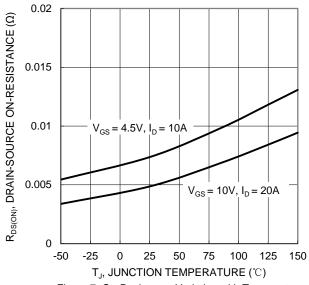
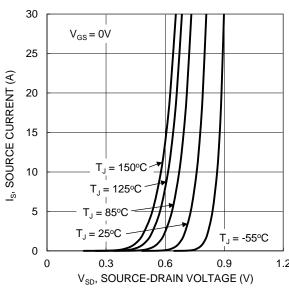


Figure 7. On-Resistance Variation with Temperature



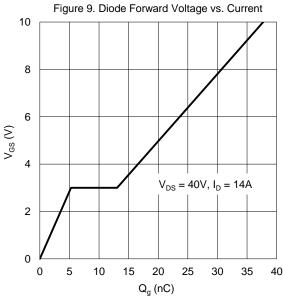


Figure 11. Gate Charge

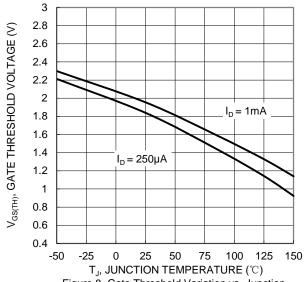
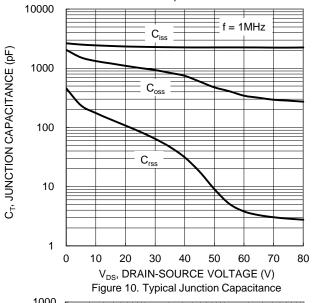


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} $P_w = 100 \mu s$ 100 ID, DRAIN CURRENT (A) 10 $P_W = 10ms$ $T_{J(Max)} = 150$ °C $T_{\rm C} = 25^{\circ}{\rm C}$ Single Pulse = 1s DUT on 1*inch ΞP Copper $V_{GS} = 10V$ 0.01 0.1 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



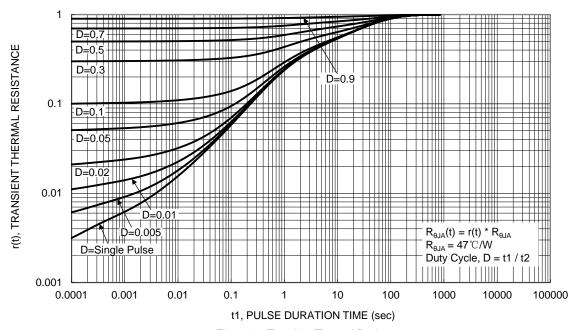


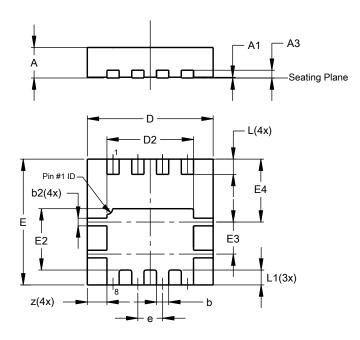
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

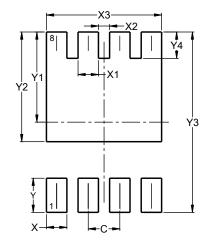


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	I	Ī	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z		_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Y	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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